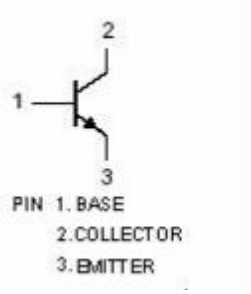
SPTECH Silicon NPN Power Transistor

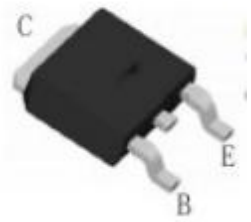
DESCRIPTION

- High Voltage: V_{CEV}= 300V(Min)
- Low Saturation Voltage-
  : $V_{CE(sat)}$= 1.0V(Max.)@ I_C= 5A



APPLICATIONS

- Designed for use in horizontal deflection output stages of TV's and CRT's



Package Type
TO-252

ABSOLUTE MAXIMUM RATINGS(T_a= 25 C)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector- Base Voltage	300	V
V_{CEO}	Collector- Emitter Voltage	150	V
V_{EBO}	Emitter- Base Voltage	6	V
I_C	Collector Current- Continuous	7	A
I_{CP}	Collector Current- Peak Repetitive	10	A
I_{CP}	Collector Current- Peak (10ms)	15	A
I_B	Base Current	4	A
P_C	Collector Power Dissipation @ T_C=25C	65	W
T_J	Junction Temperature	150	C
T_{stg}	Storage Temperature Range	-55~150	C

THERMAL CHARACTERISTICS

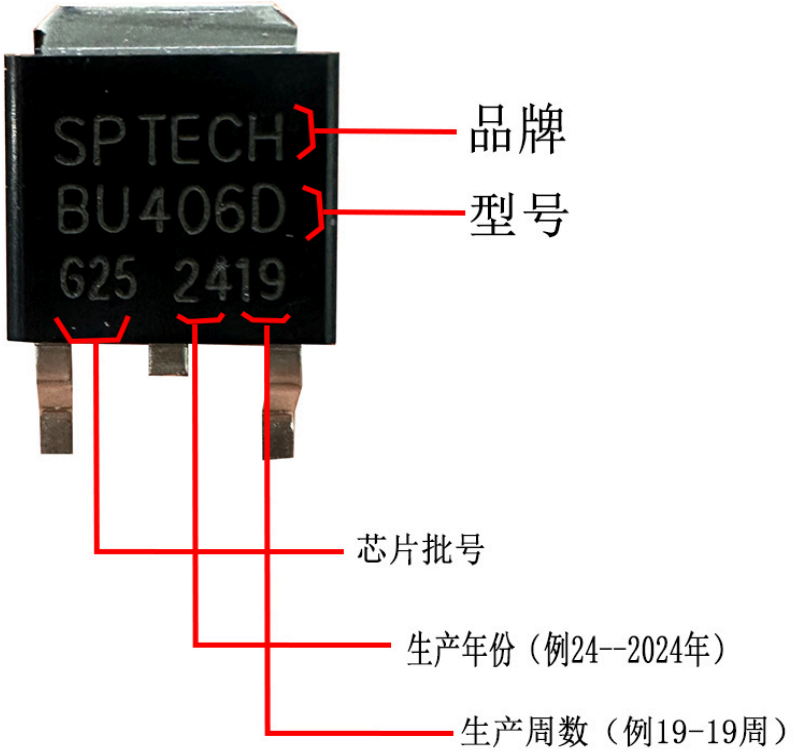
SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}c}$	Thermal Resistance, Junction to Case	2.08	C/ W
$R_{th\ j\text{-}a}$	Thermal Resistance, Junction to Ambient	70	C/ W

SPTECH Silicon NPN Power Transistor

ELECTRICAL CHARACTERISTICS

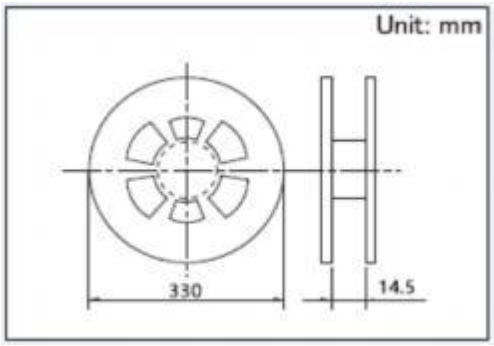
T_C= 25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector- Emitter Sustaining Voltage	I_C= 50mA ;I_B= 0	150			V
$V_{CE(sat)}$	Collector- Emitter Saturation Voltage	I_C= 5A; I_B= 0.8A			1.0	V
$V_{BE(sat)}$	Base- Emitter Saturation Voltage	I_C= 5A; I_B= 0.5A			1.2	V
I_{CES}	Collector Cutoff Current	V_{CE}= 300V; V_{BE}= 0 V_{CE}=150V; V_{BE}= 0			5.0 0.1	mA
I_{EBO}	Emitter Cutoff Current	V_{EB}= 6V; I_C= 0			1.0	mA
h_{FE}	DC Current Gain	I_C= 2A; V_{CE} = 5V	60	70	80	
f_T	Current- Gain— Bandwidth Product	I_C= 0.5A; V_{CE}= 10V	10	30		MHz
t_f	Fall Time	I_C= 5A; I_{B1}= -I_{B2}= 0.8A			0.4	μs



包装规格

载带：

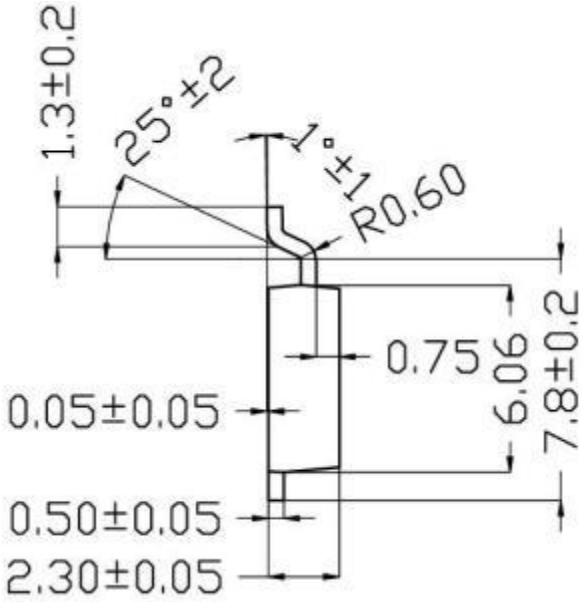


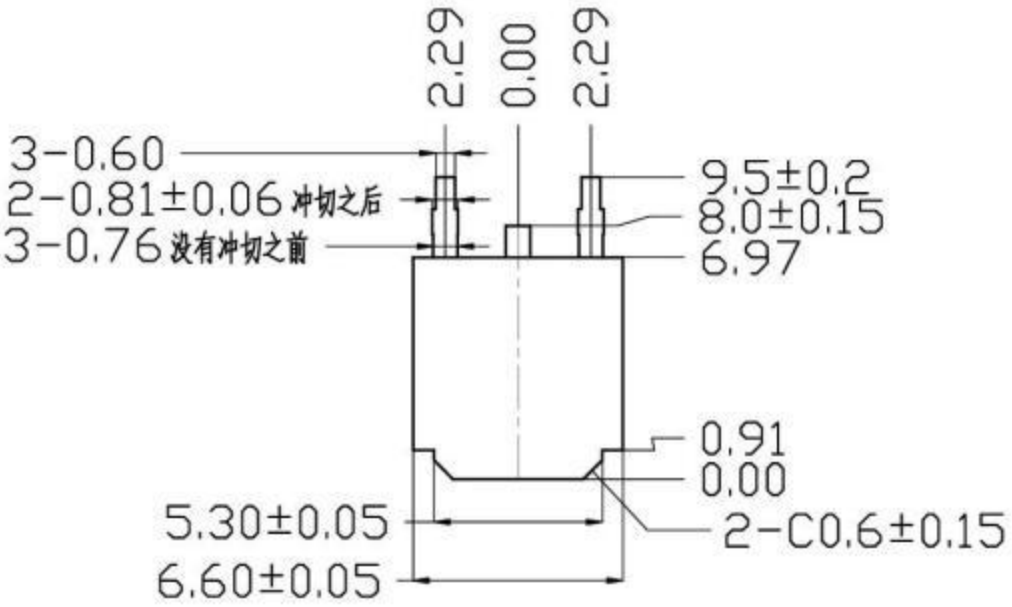
包装数量（PCS）：

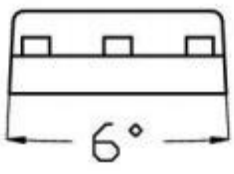
一卷	2500
一盒	5000
一箱	20000

包装尺寸(mm)：

盒装	338*338*35
箱装	360*360*45


1.3±0.2
25°±2
1°±1
R0.60
0.75
6.06
7.8±0.2
0.05±0.05
0.50±0.05
2.30±0.05


2.29
0.00
2.29
3-0.60
2-0.81±0.06 冲切之后
3-0.76 没有冲切之前
9.5±0.2
8.0±0.15
6.97
0.91
0.00
5.30±0.05
6.60±0.05
2-C0.6±0.15


6°